Amendments to the Abstract:

Pursuant to Rule 1.72, the attached abstract includes the changes to the abstract as indicted below.

Abstract

A substrate is set on a susceptor installed in a reactor and arranged horizontally. Then, a A cooling jacket is provided at the opposite a portion of the inner wall of the reactor that is opposite to the substrate. By flowing a given cooling medium through the cooling jacket with a pump connected to the jacket, at least the opposite portion of the inner wall is cooled down, to inhibit which inhibits the reaction between raw material gases introduced into the reactor. As a result, in fabricating a III-V nitride film, the film growth rate is developed and the crystal quality is developed.

Attachment: Replacement Sheet - Abstract

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Abstract

A substrate is set on a susceptor installed in a reactor and arranged horizontally. A cooling jacket is provided at a portion of the inner wall of the reactor that is opposite to the substrate. By flowing a given cooling medium through the cooling jacket with a pump connected to the jacket, at least the opposite portion of the inner wall is cooled down, which inhibits the reaction between raw material gases introduced into the reactor. As a result, in fabricating a III-V nitride film, the film growth rate is developed and the crystal quality is developed.